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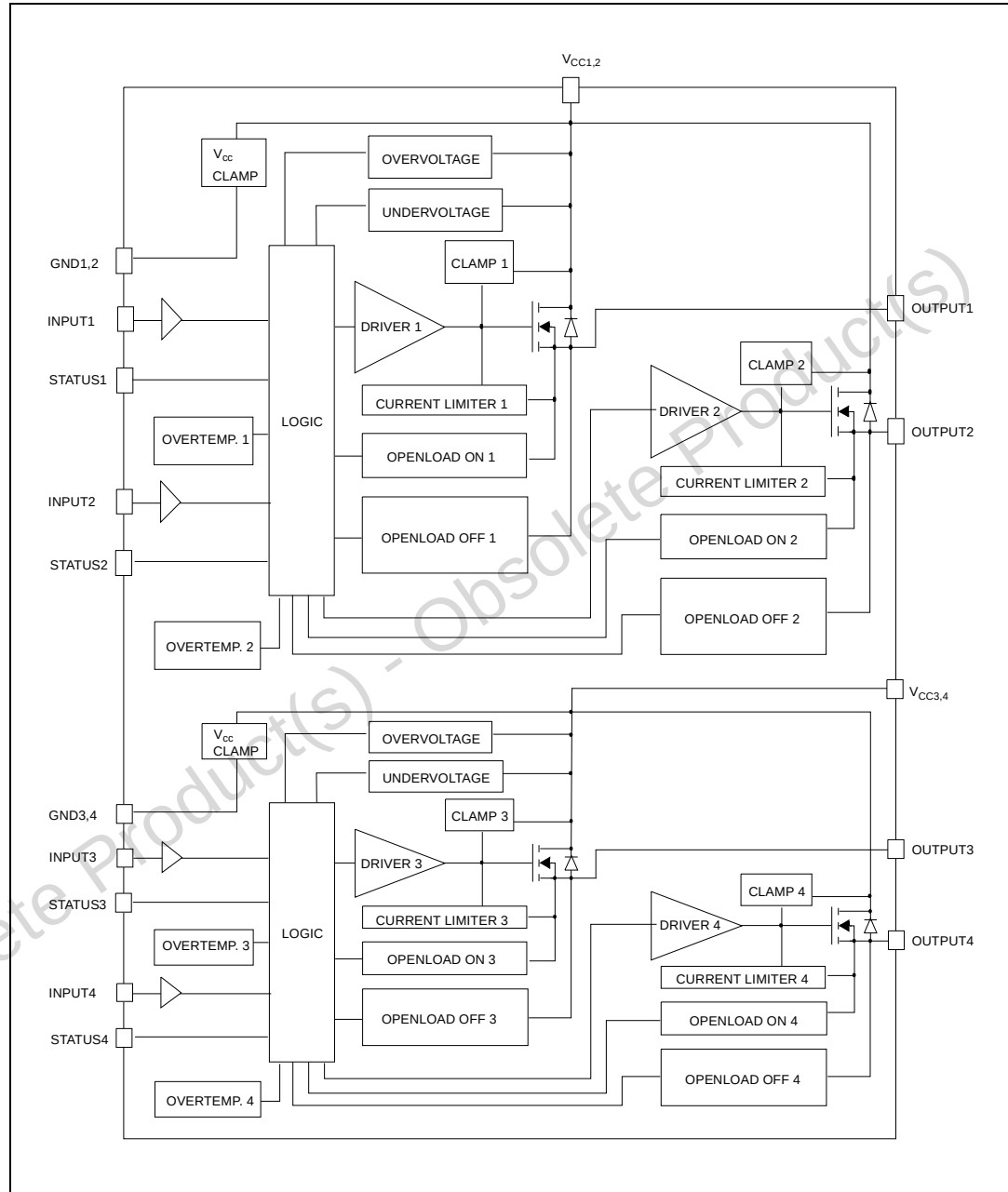
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1 Block diagram and pin description

Figure 1. Block diagram



V _{CC} 1,2	1	28	V _{CC} 1,2
GND 1,2			OUTPUT1
INPUT1			OUTPUT1
STATUS1			OUTPUT1
STATUS2			OUTPUT2
INPUT2			OUTPUT2
V _{CC} 1,2			OUTPUT2
V _{CC} 3,4			OUTPUT3
GND 3,4			OUTPUT3
INPUT3			OUTPUT3
STATUS3			OUTPUT4
STATUS4			OUTPUT4
INPUT4			OUTPUT4
V _{CC} 3,4	14	15	V _{CC} 3,4

Connection / pin	Status	N.C.	Output	Input
Floating	X	X	X	X
To ground		X		Through 10K Ω resistor

2 Electrical specifications

2.1 Absolute maximum ratings

Stressing the device above the rating listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality document.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	41	V
$-V_{CC}$	Reverse DC supply voltage	-0.3	V
$-I_{GND}$	DC reverse ground pin current	-200	mA
I_{OUT}	DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	-6	A
I_{IN}	DC input current	+/- 10	mA
I_{STAT}	DC Status current	+/- 10	mA
V_{ESD}	Electrostatic discharge (human body model: $R=1.5K\Omega$; $C = 100pF$)		
	– INPUT	4000	V
	– STATUS	4000	V
	– OUTPUT	5000	V
	– V_{CC}	5000	V
E_{MAX}	Maximum switching energy ($L = 2.5\text{ mH}$; $R_L = 0\ \Omega$; $V_{bat} = 13.5\text{ V}$; $T_{jstart} = 150\text{ }^\circ\text{C}$; $I_L = 9\text{ A}$)	140	mJ
P_{tot}	Power dissipation (per island) at $T_{lead} = 25\text{ }^\circ\text{C}$	6.25	W
T_j	Junction operating temperature	Internally limited	$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$

2.2 Thermal data

Table 4. Thermal data (per island)

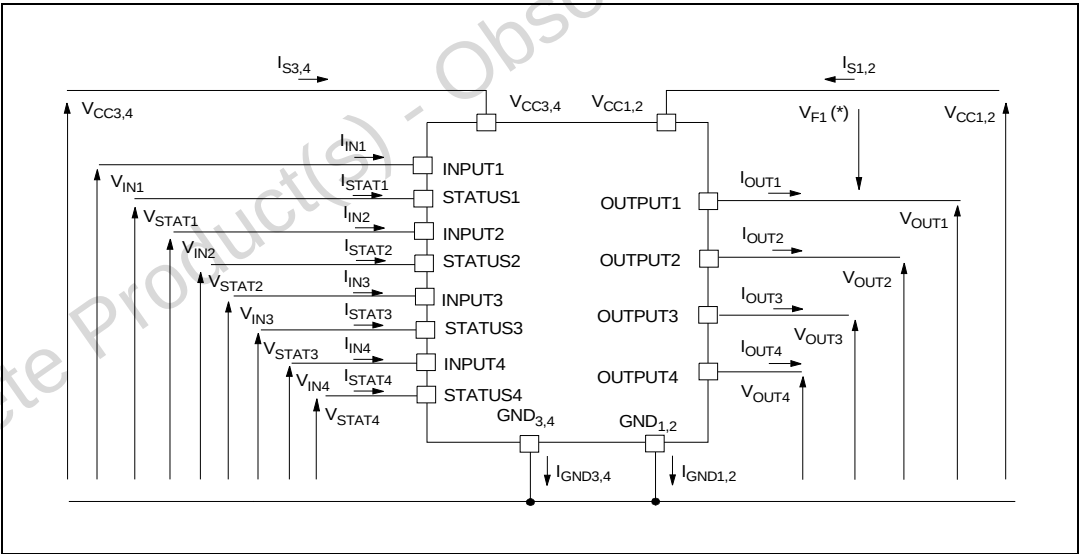
Symbol	Parameter	Value		Unit
$R_{thj-lead}$	Thermal resistance junction-lead	20		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (one chip ON)	60 ⁽¹⁾	44 ⁽²⁾	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (two chips ON)	46 ⁽¹⁾	31 ⁽²⁾	°C/W

1. When mounted on a standard single-sided FR-4 board with 0.5cm² of Cu (at least 35 μm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.
2. When mounted on a standard single-sided FR-4 board with 6cm² of Cu (at least 35 μm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.

2.3 Electrical characteristics

Values specified in this section are for 8V < V_{CC} < 36V; -40 °C < T_j < 150 °C, unless otherwise stated.

Figure 3. Current and voltage conventions



Note: $V_{Fn} = V_{CCn} - V_{OUTn}$ during reverse battery condition.



Table 5. Power

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC}	Operating supply voltage		5.5	13	36	V
V_{USD}	Undervoltage shutdown		3	4	5.5	V
V_{OV}	Overvoltage shutdown		36			V
R_{ON}	On-state resistance	$I_{OUT} = 2\text{ A}; T_j = 25\text{ °C}$			65	mΩ
		$I_{OUT} = 2\text{ A}; V_{CC} > 8\text{ V}$			130	mΩ
I_S	Supply current	Off-state; $V_{CC} = 13\text{ V}; V_{IN} = V_{OUT} = 0\text{ V}$		12	40	μA
		Off-state; $V_{CC} = 13\text{ V}; V_{IN} = V_{OUT} = 0\text{ V}; T_j = 25\text{ °C}$		12	25	μA
		On-state; $V_{CC} = 13\text{ V}; V_{IN} = 5\text{ V}; I_{OUT} = 0\text{ A}$		5	7	mA
$I_{L(off1)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}$	0		50	μA
$I_{L(off2)}$	Off-state output current	$V_{IN} = 0\text{ V}; V_{OUT} = 3.5\text{ V}$	-75		0	μA
$I_{L(off3)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}; V_{CC} = 13\text{ V}; T_j = 125\text{ °C}$			5	μA
$I_{L(off4)}$	Off-state output current	$V_{IN} = V_{OUT} = 0\text{ V}; V_{CC} = 13\text{ V}; T_j = 25\text{ °C}$			3	μA

Table 6. Protections

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T_{TSD}	Shutdown temperature		150	175	200	°C
T_R	Reset temperature		135			°C
T_{hyst}	Thermal hysteresis		7	15		°C
t_{SDL}	Status delay in overload conditions	$T_j > T_{TSD}$			20	μs
I_{lim}	Current limitation	$V_{CC} = 13\text{ V}$	6	9	15	A
		$5.5\text{ V} < V_{CC} < 36\text{ V}$			15	A
V_{demag}	Turn-off output clamp voltage	$I_{OUT} = 2\text{ A}; L = 6\text{ mH}$	$V_{CC} - 41$	$V_{CC} - 48$	$V_{CC} - 55$	V

Note: To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device is subjected to abnormal conditions, this software must limit the duration and number of activation cycles.

Table 7. V_{CC} - output diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on voltage	$-I_{OUT} = 1.2\text{ A}; T_j = 150\text{ °C}$	—	—	0.6	V

Table 8. Switching ($V_{CC} = 13\text{ V}$; $T_j = 25\text{ °C}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$R_L = 6.5\ \Omega$ from V_{IN} rising edge to $V_{OUT} = 1.3\text{ V}$ (see Figure 5)	—	30	—	μs
$t_{d(off)}$	Turn-off delay time	$R_L = 6.5\ \Omega$ from V_{IN} falling edge to $V_{OUT} = 11.7\text{ V}$ (see Figure 5)	—	30	—	μs
$dV_{OUT}/dt_{(on)}$	Turn-on voltage slope	$R_L = 6.5\ \Omega$ from $V_{OUT} = 1.3\text{ V}$ to $V_{OUT} = 10.4\text{ V}$ (see Figure 5)	—	See Figure 10	—	$\text{V}/\mu\text{s}$
$dV_{OUT}/dt_{(off)}$	Turn-off voltage slope	$R_L = 6.5\ \Omega$ from $V_{OUT} = 11.7\text{ V}$ to $V_{OUT} = 1.3\text{ V}$ (see Figure 5)	—	See Figure 12	—	$\text{V}/\mu\text{s}$

Table 9. Logic inputs

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IL}	Input low level				1.25	V
I_{IL}	Low level input current	$V_{IN} = 1.25\text{ V}$	1			μA
V_{IH}	Input high level		3.25			V
I_{IH}	High level input current	$V_{IN} = 3.25\text{ V}$			10	μA
$V_{I(hyst)}$	Input hysteresis voltage		0.5			V
V_{ICL}	Input clamp voltage	$I_{IN} = 1\text{ mA}$	6	6.8	8	V
		$I_{IN} = -1\text{ mA}$		-0.7		V

Table 10. Status pin

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{STAT}	Status low output voltage	$I_{STAT} = 1.6\text{ mA}$			0.5	V
I_{LSTAT}	Status leakage current	Normal operation; $V_{STAT} = 5\text{ V}$			10	μA
C_{STAT}	Status pin Input capacitance	Normal operation; $V_{STAT} = 5\text{ V}$			100	pF
V_{SCL}	Status clamp voltage	$I_{STAT} = 1\text{ mA}$	6	6.8	8	V
		$I_{STAT} = -1\text{ mA}$		-0.7		V

Table 11. Open-load detection

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{OL}	Open-load on-state detection threshold	$V_{IN} = 5\text{ V}$	50	100	200	mA
$t_{DOL(on)}$	Open-load on-state detection delay	$I_{OUT} = 0\text{ A}$			200	μs
V_{OL}	Open-load off-state voltage detection threshold	$V_{IN} = 0\text{ V}$	1.5	2.5	3.5	V
$t_{DOL(off)}$	Open-load detection delay at turn-off				1000	μs

Figure 4. Status timings

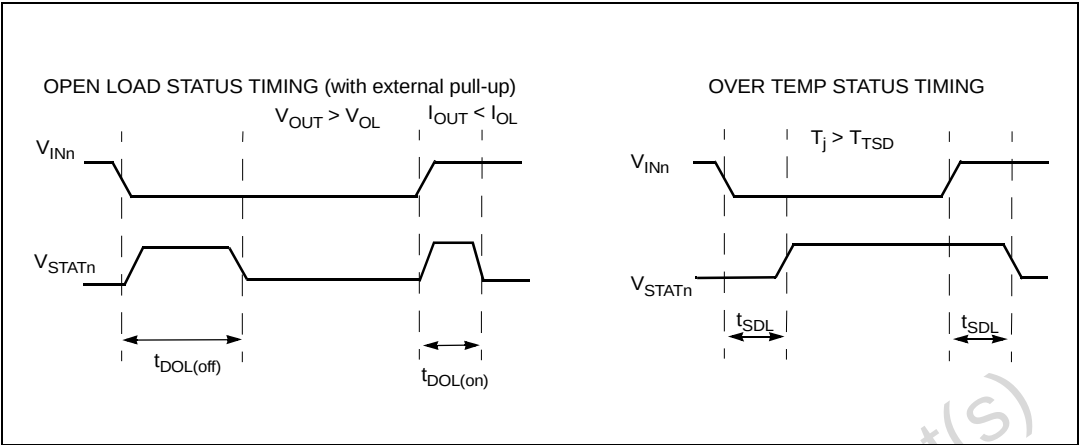


Figure 5. Switching characteristics

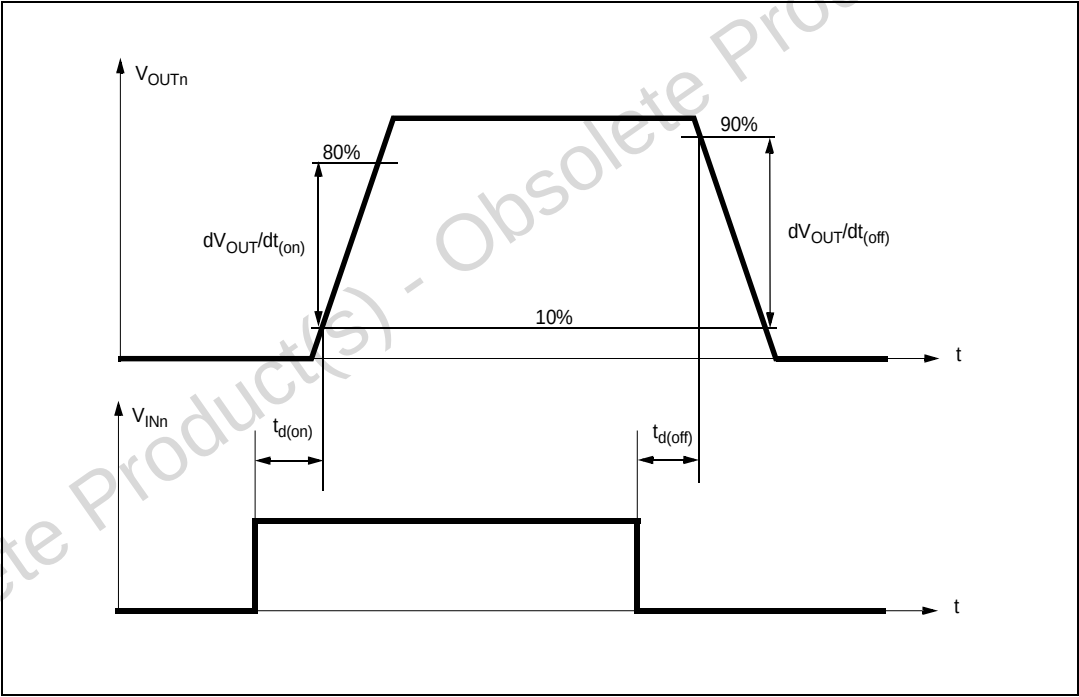


Table 12. Truth table

Conditions	Input	Output	Status
Normal operation	L	L	H
	H	H	H
Current limitation	L	L	H
	H	X	$(T_j < T_{TSD})$ H
	H	X	$(T_j > T_{TSD})$ L
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output voltage > V_{OL}	L	H	L
	H	H	H
Output current < I_{OL}	L	L	H
	H	H	L

Table 13. Electrical transient requirements (part 1)

ISO T/R 7637/1 Test pulse	Test level				
	I	II	III	IV	Delays and impedance
1	- 25V	- 50V	- 75V	- 100V	2ms, 10Ω
2	+ 25V	+ 50V	+ 75V	+ 100V	0.2ms, 10Ω
3a	- 25V	- 50V	- 100V	- 150V	0.1μs, 50Ω
3b	+ 25V	+ 50V	+ 75V	+ 100V	0.1μs, 50Ω
4	- 4V	- 5V	- 6V	- 7V	100ms, 0.01Ω
5	+ 26.5V	+ 46.5V	+ 66.5V	+ 86.5V	400ms, 2Ω

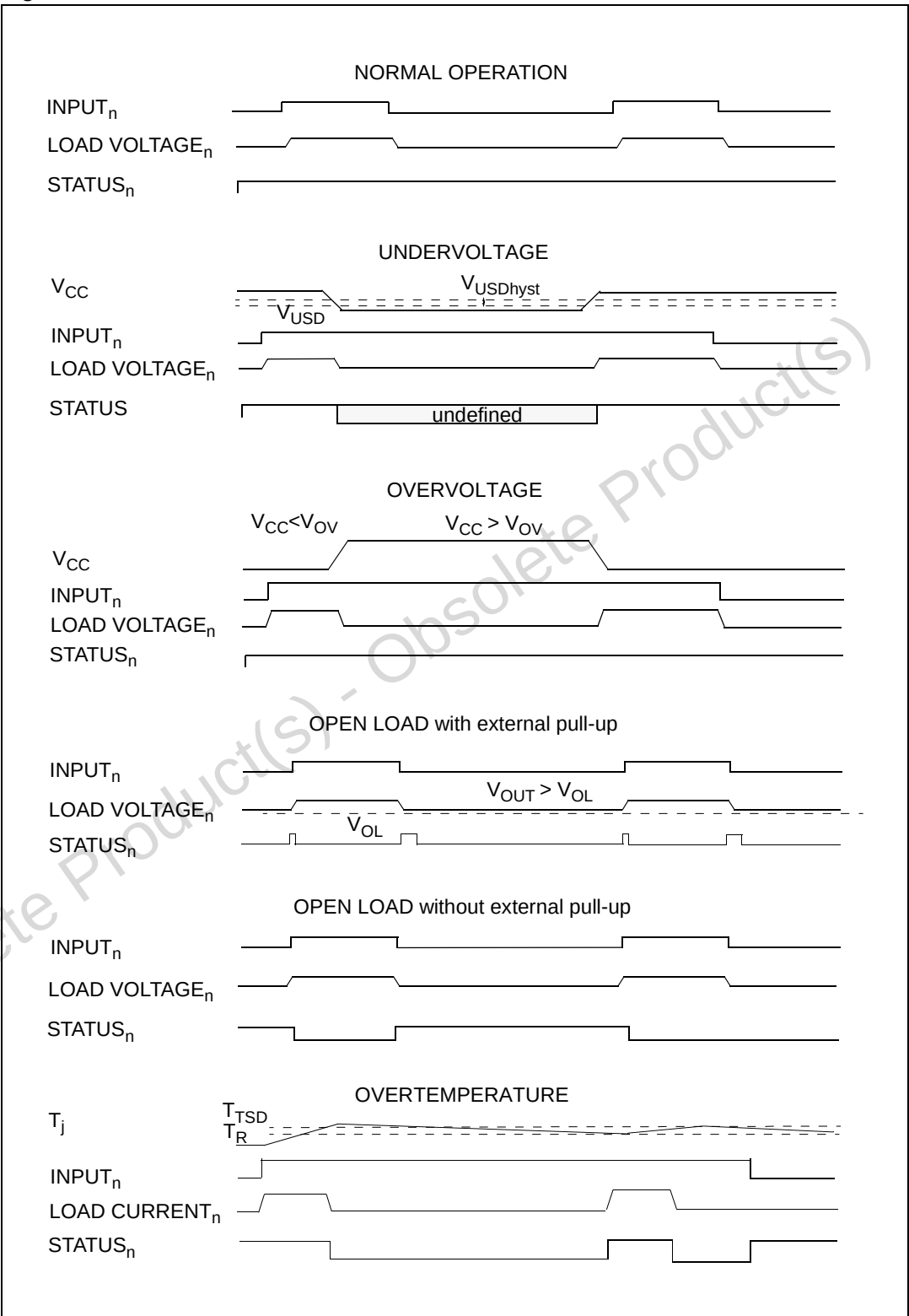
Table 14. Electrical transient requirements (part 2)

ISO T/R 7637/1 Test pulse	Test level			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

Table 15. Electrical transient requirements (part 3)

Class	Contents
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

Figure 6. Waveforms



2.4 Electrical characteristics curves

Figure 7. Off-state output current

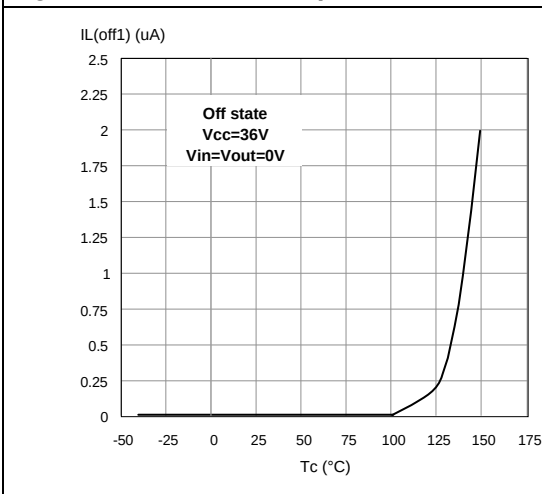


Figure 8. High level input current

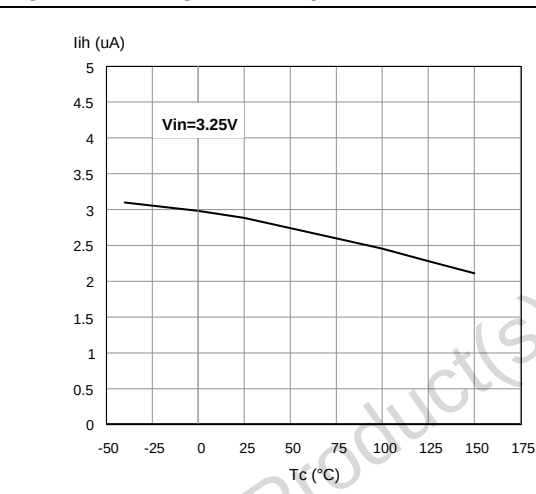


Figure 9. Input clamp voltage

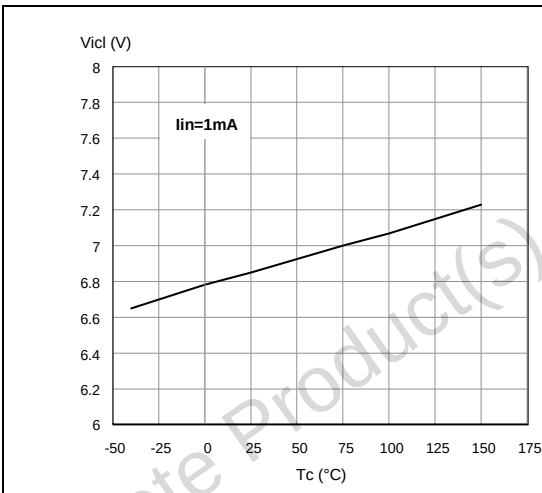


Figure 10. Turn-on voltage slope

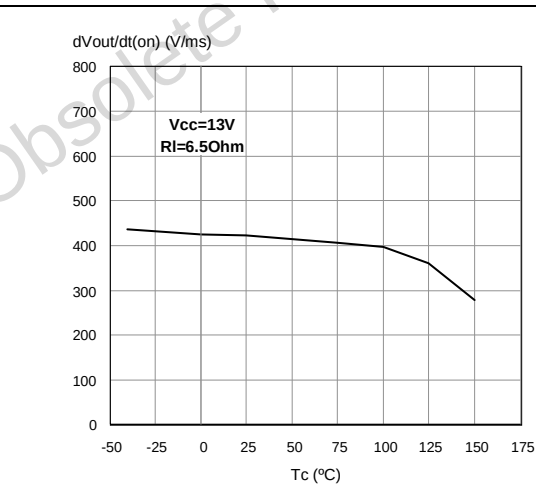


Figure 11. Overvoltage shutdown

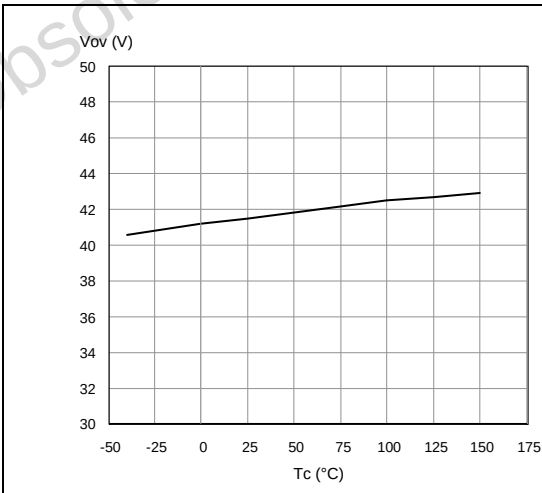


Figure 12. Turn-off voltage slope

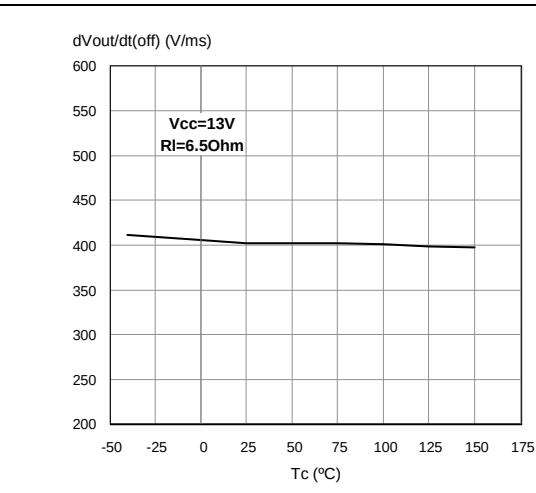


Figure 13. I_{LIM} vs T_{case}

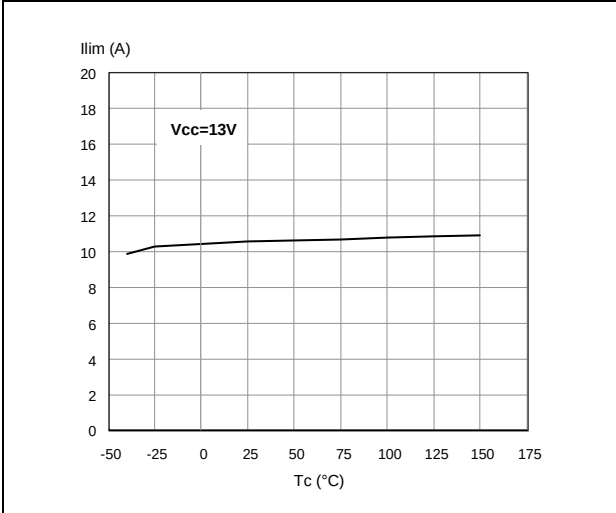


Figure 14. On-state resistance vs V_{CC}

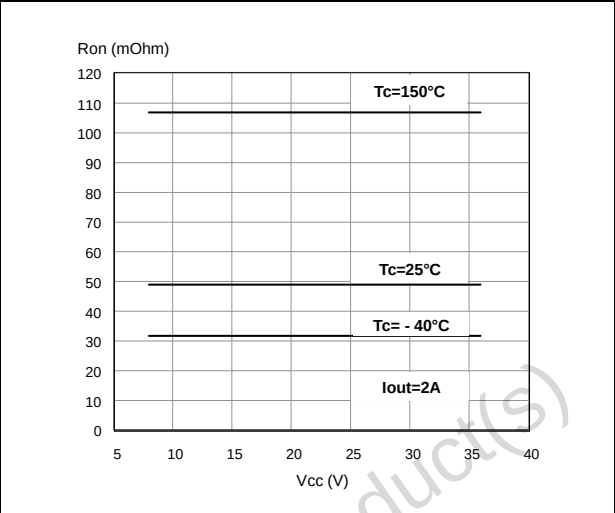


Figure 15. Input high level

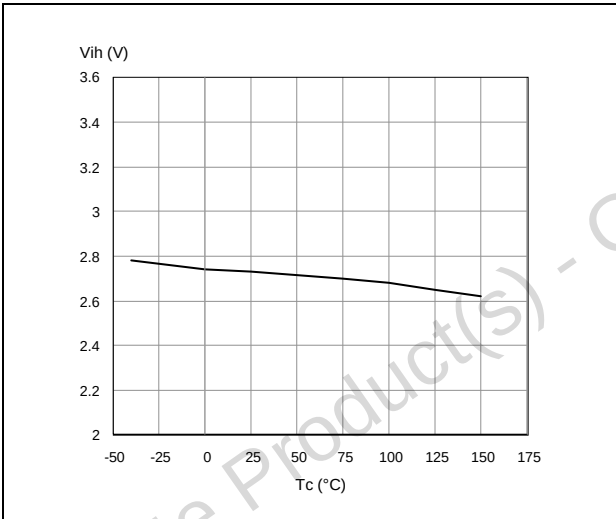


Figure 16. Input hysteresis voltage

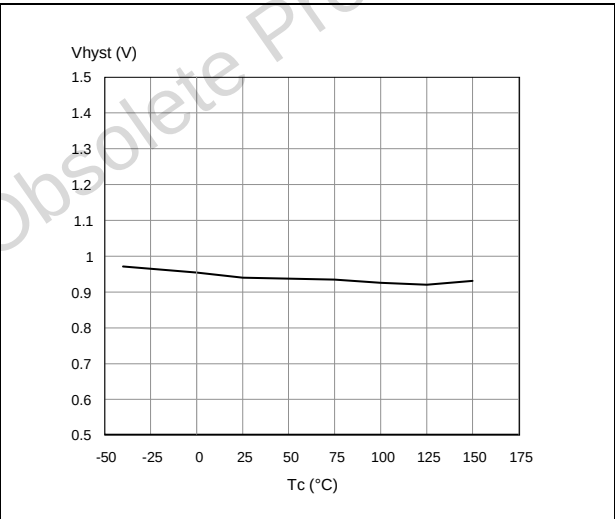


Figure 17. On-state resistance vs T_{case}

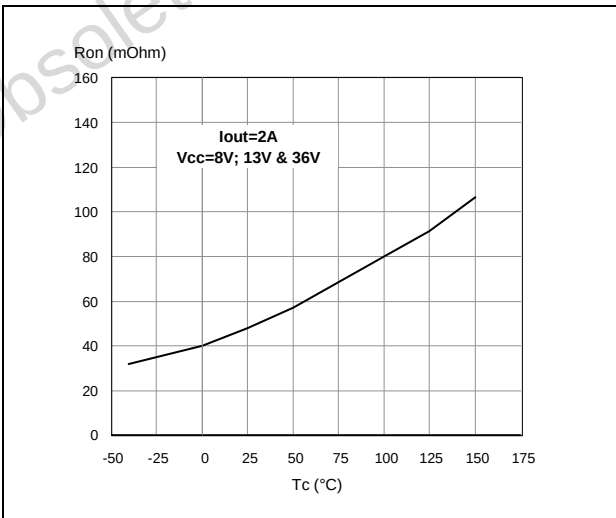


Figure 18. Input low level

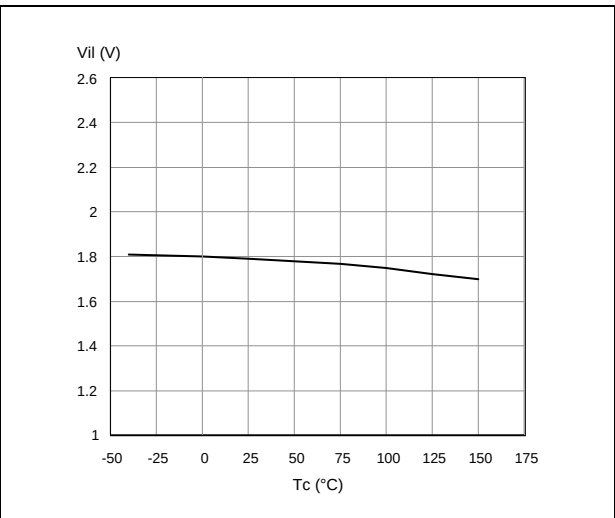


Figure 19. Status leakage current

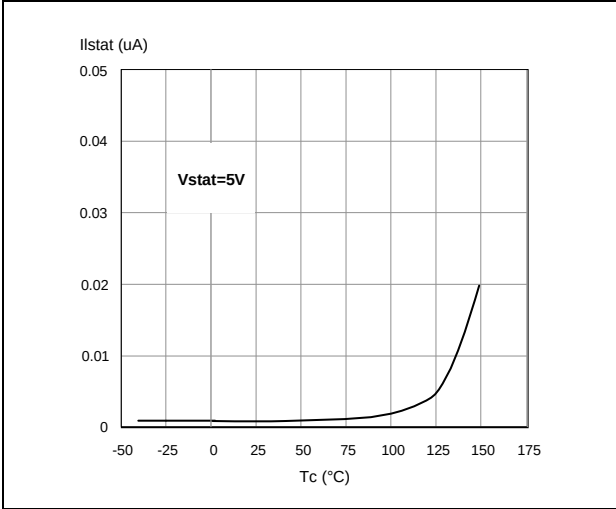


Figure 20. Status low output voltage

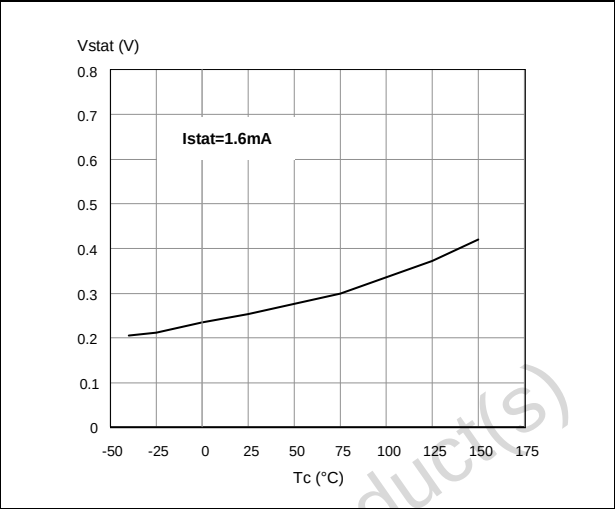


Figure 21. Status clamp voltage

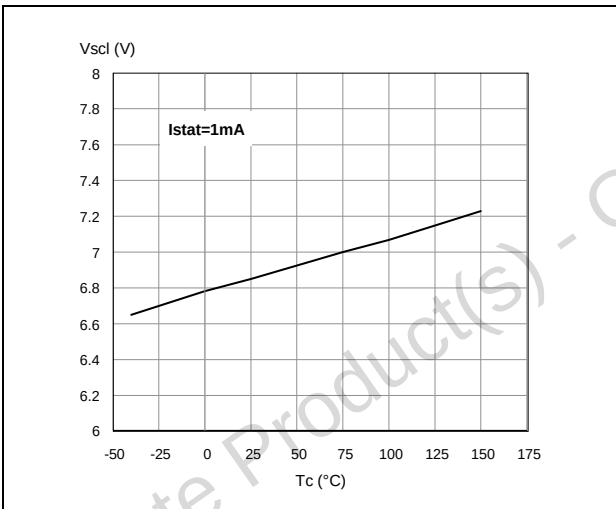


Figure 22. Open-load on-state detection threshold

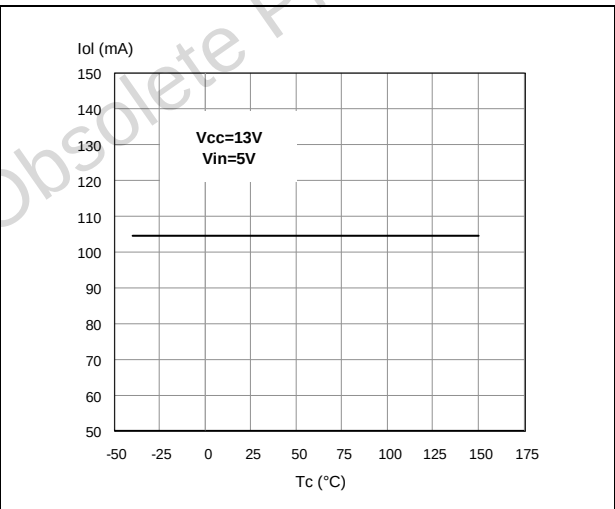
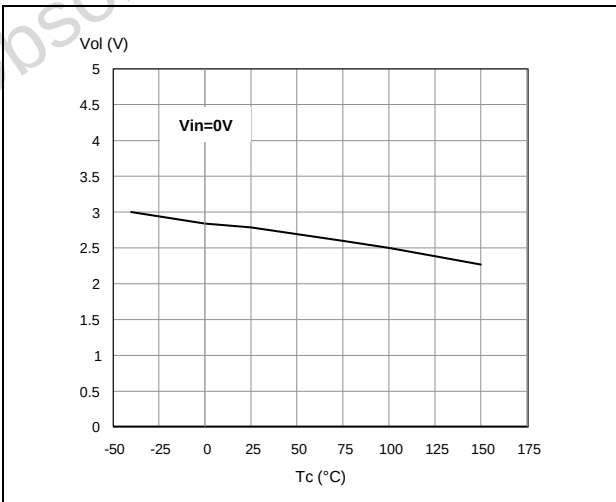
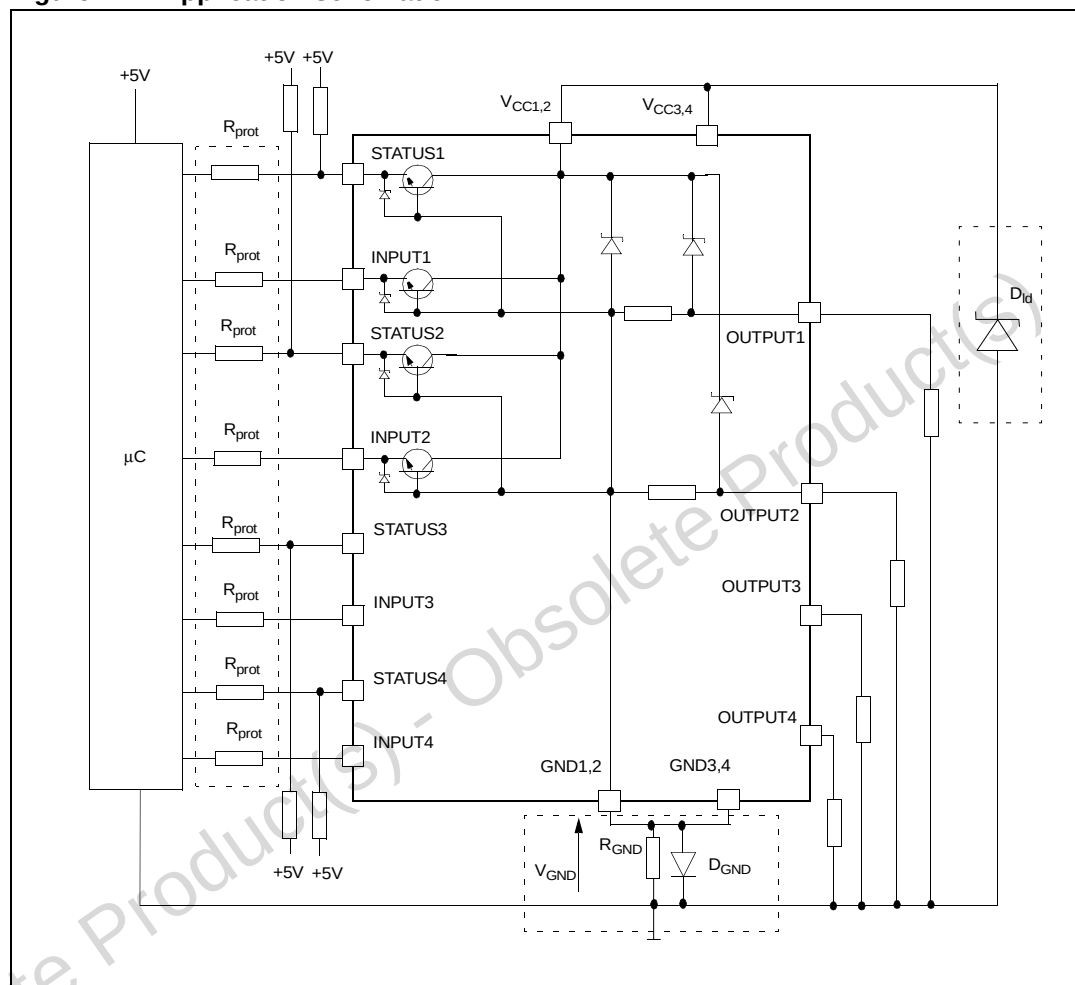


Figure 23. Open-load off-state voltage detection threshold



3 Application information

Figure 24. Application schematic



Note: Channels 3 and 4 have the same internal circuit as channel 1 and 2.

3.1 GND protection network against reverse battery

This section provides two solutions for implementing a ground protection network against reverse battery.

3.1.1 Solution 1: a resistor in the ground line (R_{GND} only)

This can be used with any type of load.

The following show how to dimension the R_{GND} resistor:

1. $R_{GND} \leq 600 \text{ mV} / 2(I_{S(on)max})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0$ during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that, if the microprocessor ground is not shared by the device ground, then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation requires the use of a large resistor, or several devices have to share the same resistor, then ST suggests using solution 2 below.

3.1.2 Solution 2: a diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 1 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load. This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift ($\approx 600 \text{ mV}$) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network. Series resistor in INPUT and STATUS lines are also required to prevent that, during battery voltage transient, the current exceeds the Absolute Maximum Rating. Safest configuration for unused INPUT and STATUS pin is to leave them unconnected.

3.2 Load dump protection

D_{ld} is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the V_{CC} maximum DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than those shown in the ISO T/R 7637/1 table.

3.3 MCU I/O protection

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the microcontroller I/O pins from latching up.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit microcontroller I/Os:

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Example

For the following conditions:

$$V_{CCpeak} = -100 \text{ V}$$

$$I_{latchup} \geq 20 \text{ mA}$$

$$V_{OH\mu C} \geq 4.5 \text{ V}$$

$$5 \text{ k}\Omega \leq R_{prot} \leq 65 \text{ k}\Omega.$$

Recommended values are:

$$R_{prot} = 10 \text{ k}\Omega$$

3.4 Open load detection in off-state

Off-state open load detection requires an external pull-up resistor (R_{PU}) connected between OUTPUT pin and a positive supply voltage (V_{PU}) like the +5V line used to supply the microprocessor.

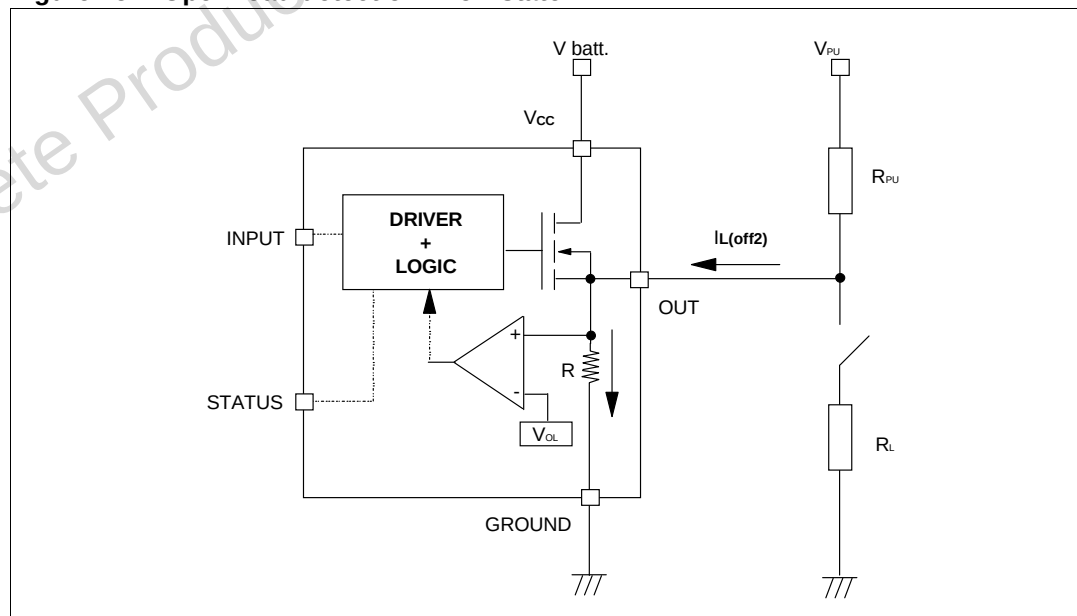
The external resistor has to be selected according to the following requirements:

1. No false open load indication when load is connected: in this case we have to avoid V_{OUT} to be higher than V_{OLmin} ; this results in the following condition

$$V_{OUT} = (V_{PU} / (R_L + R_{PU}))R_L < V_{OLmin}.$$
2. No misdetection when load is disconnected: in this case the V_{OUT} has to be higher than V_{OLmax} ; this results in the following condition $R_{PU} < (V_{PU} - V_{OLmax}) / I_{L(off2)}.$

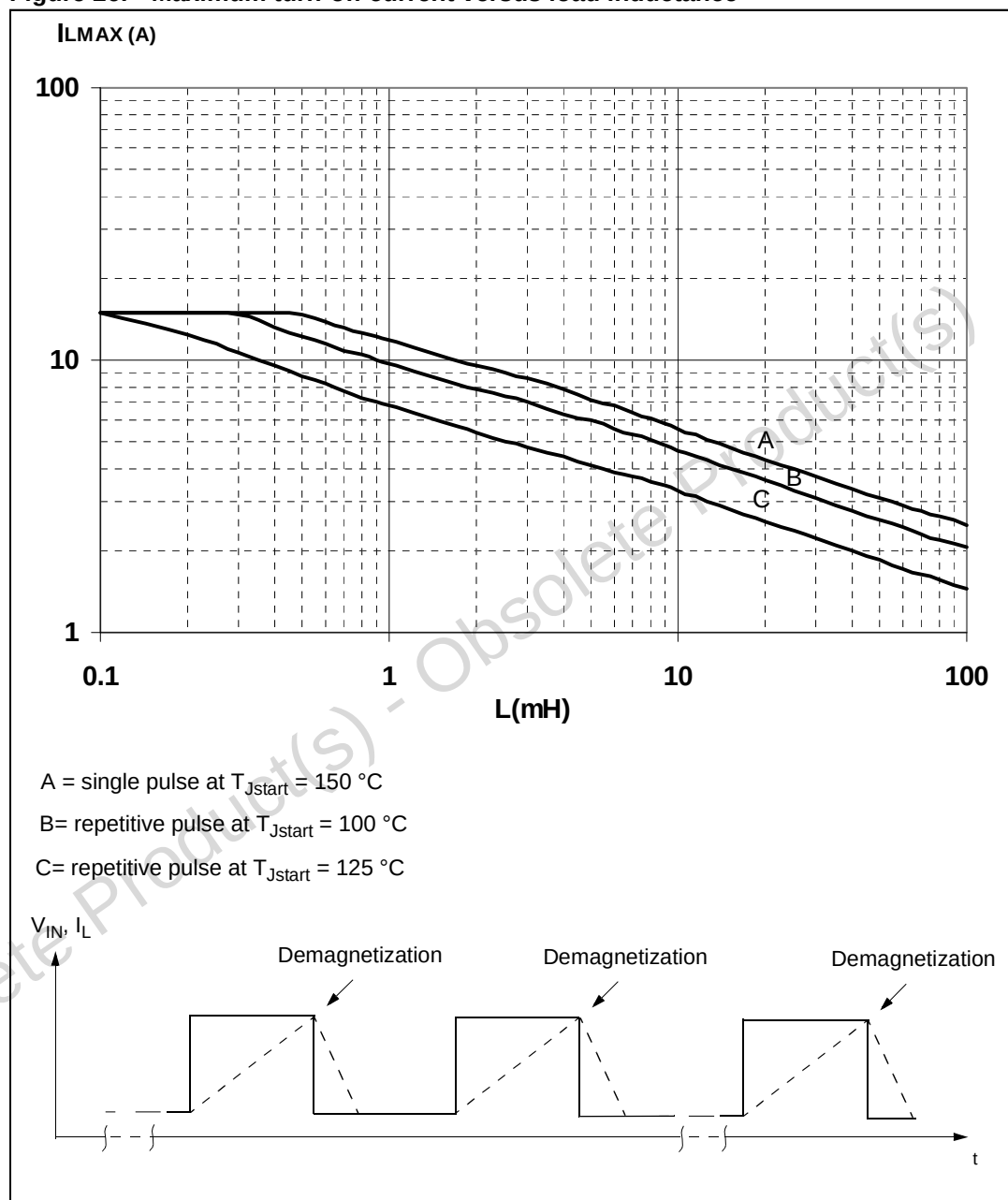
Because $I_{S(OFF)}$ may significantly increase if V_{out} is pulled high (up to several mA), the pull-up resistor R_{PU} should be connected to a supply that is switched OFF when the module is in standby.

Figure 25. Open-load detection in off-state



3.5 Maximum demagnetization energy ($V_{CC} = 13.5V$)

Figure 26. Maximum turn-off current versus load inductance



Note:

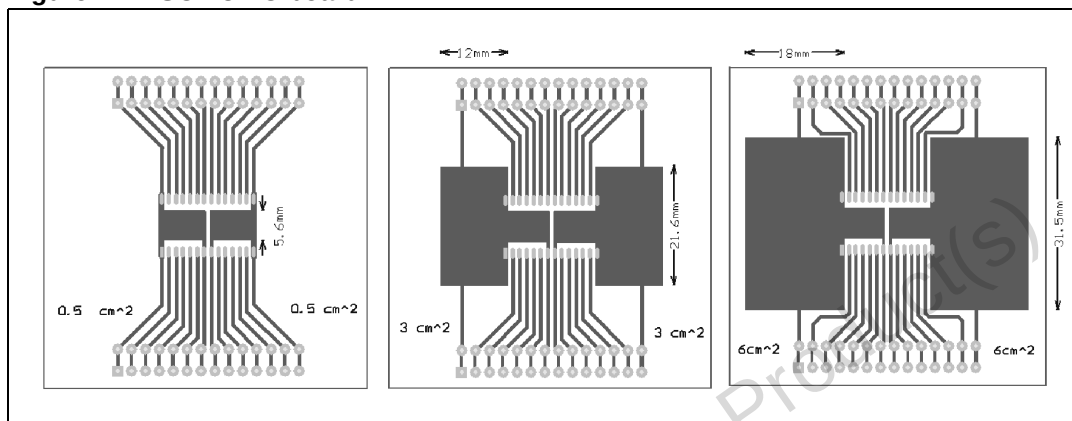
Values are generated with $R_L = 0\text{ }\Omega$.

In case of repetitive pulses, T_{Jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.

4 Package and PCB thermal data

4.1 SO-28 thermal data

Figure 27. SO-28 PC board



Note: Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area = 58mm x 58mm, PCB thickness = 2mm, Cu thickness = 35 μ m, Copper areas: 0.5 cm², 3 cm², 6 cm²).

Table 16. Thermal calculation according to the PCB heatsink area

Chip 1	Chip 2	T_{jchip1}	T_{jchip2}	Note
ON	OFF	$R_{thA} \times P_{dchip1} + T_{amb}$	$R_{thC} \times P_{dchip1} + T_{amb}$	
OFF	ON	$R_{thC} \times P_{dchip2} + T_{amb}$	$R_{thA} \times P_{dchip2} + T_{amb}$	
ON	ON	$R_{thB} \times (P_{dchip1} + P_{dchip2}) + T_{amb}$	$R_{thB} \times (P_{dchip1} + P_{dchip2}) + T_{amb}$	$P_{dchip1} = P_{dchip2}$
ON	ON	$(R_{thA} \times P_{dchip1}) + R_{thC} \times P_{dchip2} + T_{amb}$	$(R_{thA} \times P_{dchip2}) + R_{thC} \times P_{dchip1} + T_{amb}$	$P_{dchip1} \neq P_{dchip2}$

R_{thA} = thermal resistance junction to ambient with one chip ON

R_{thB} = thermal resistance junction to ambient with both chips ON and $P_{dchip1} = P_{dchip2}$

R_{thC} = mutual thermal resistance

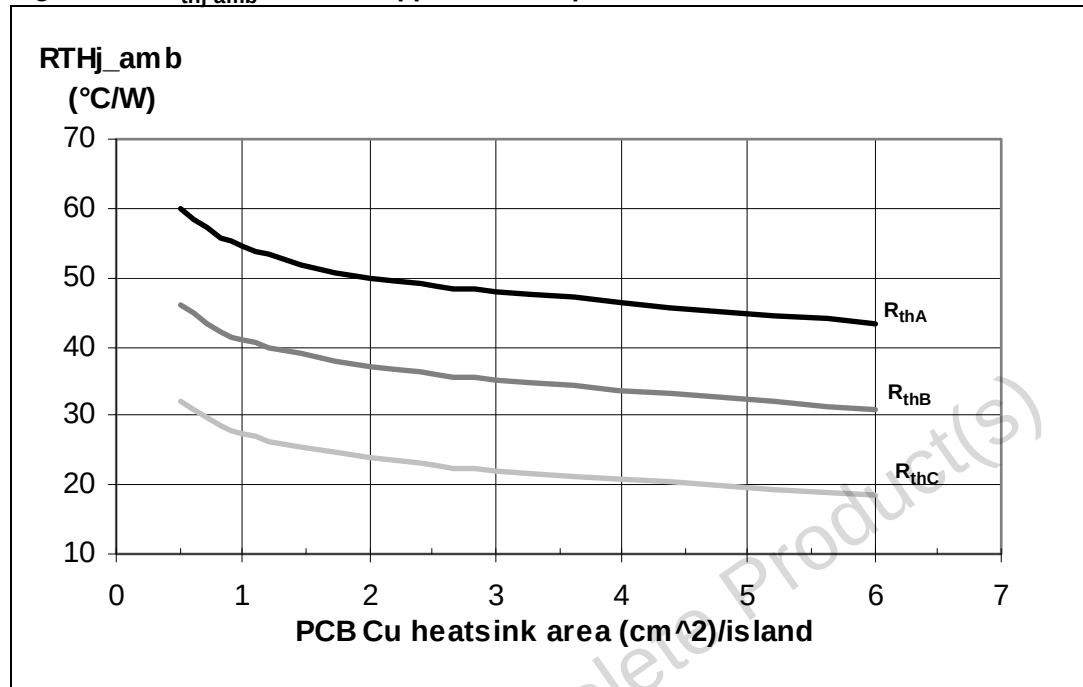
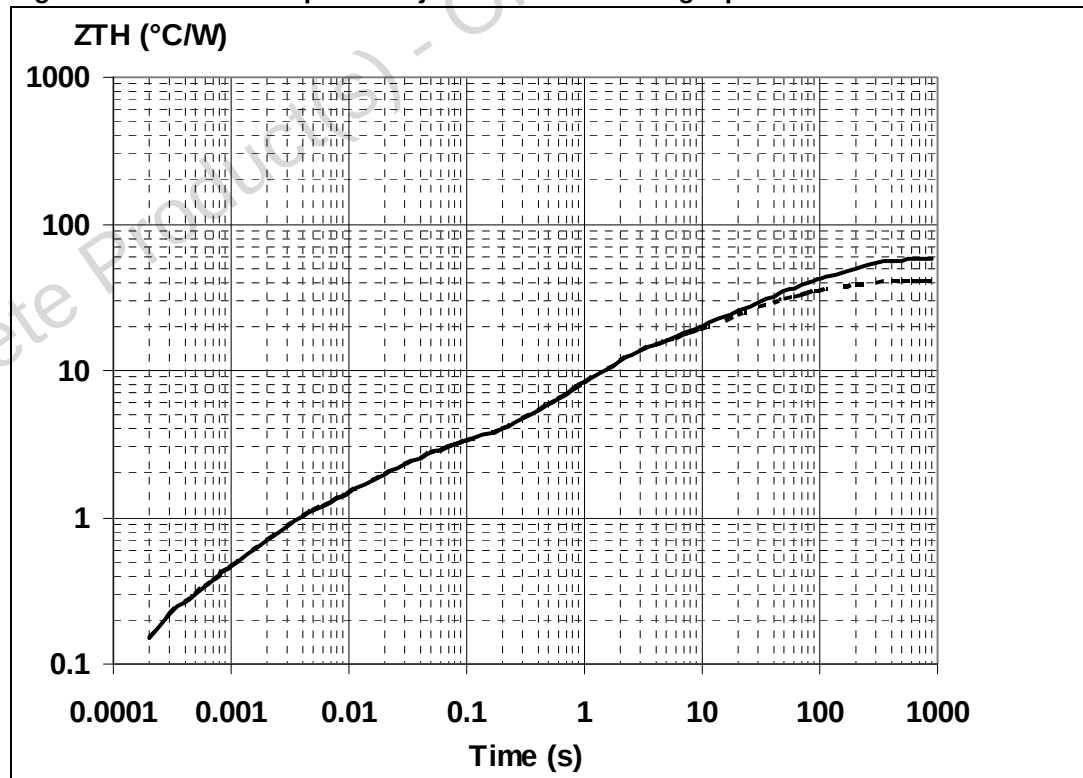
Figure 28. $R_{thj-amb}$ vs PCB copper area in open box free air condition

Figure 29. Thermal impedance junction ambient single pulse



Equation 1: pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

where $\delta = t_p/T$

Figure 30. Thermal fitting model of a quad channel HSD in SO-28

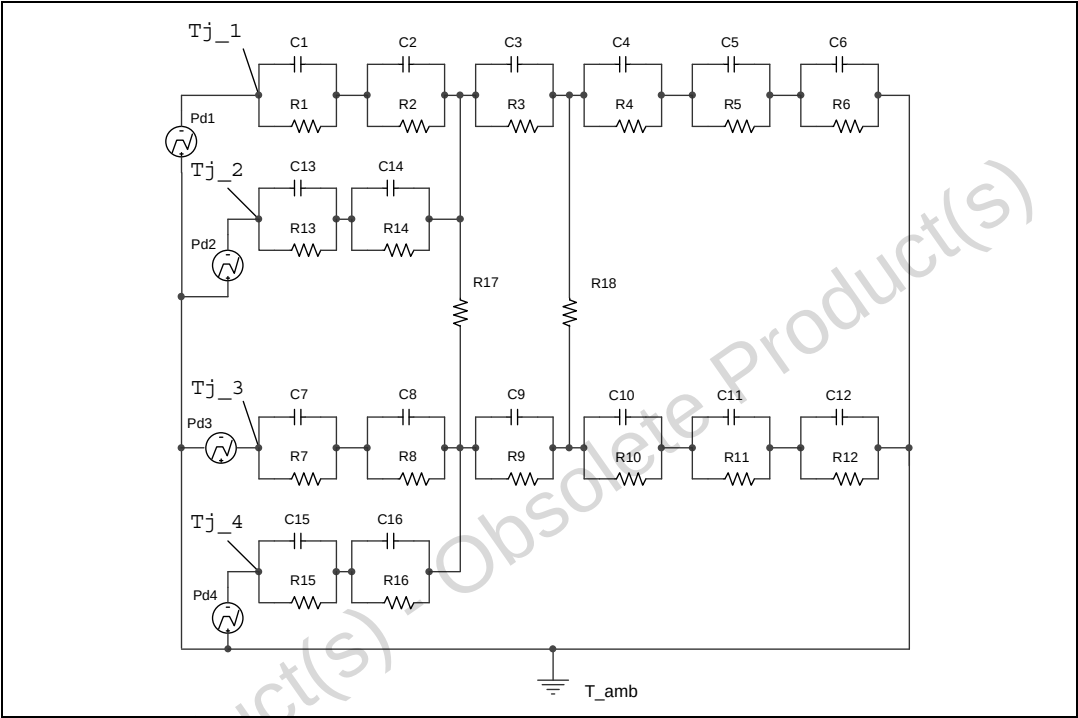


Table 17. Thermal parameters

Area / island (cm ²)	Footprint	6
R1 = R7 = R13 = R15 (°C/W)	0.15	
R2 = R8 = R14 = R16 (°C/W)	0.7	
R3 = R9 (°C/W)	1.8	
R4 = R10 (°C/W)	10	
R5 = R11 (°C/W)	15	
R6 = R12 (°C/W)	30	13
C1 = C7 = C13 = C15 (W.s/°C)	0.0005	
C2 = C8 = C14 = C16 (W.s/°C)	3E-03	
C3 = C9 (W.s/°C)	1.50E-02	
C4 = C10 (W.s/°C)	0.15	
C5 = C11 (W.s/°C)	1.5	
C6 = C12 (W.s/°C)	5	8
R17 = R18 (°C/W)	150	

5 Package and packing information

5.1 ECOPACK® packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.

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Figure 31. SO-28 package dimensions

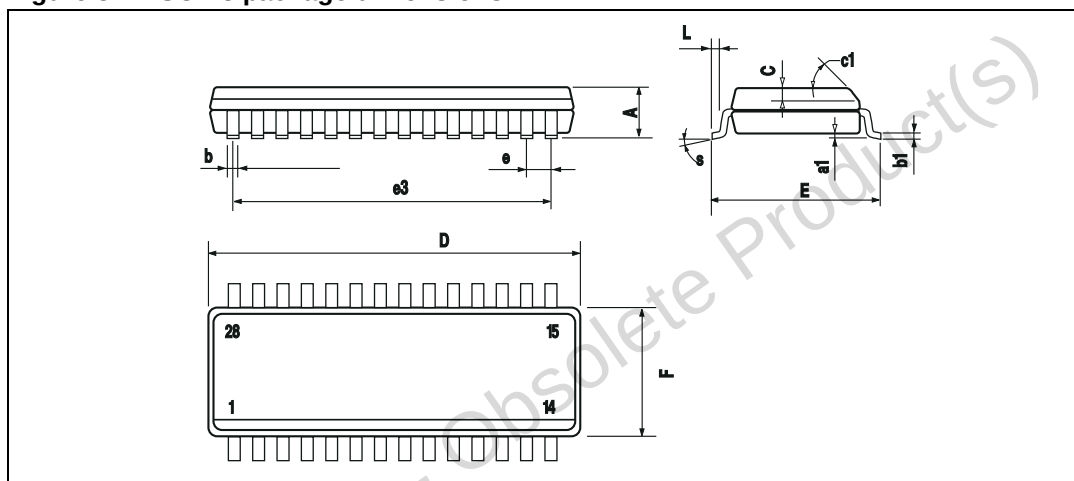


Table 18. SO-28 mechanical data

Symbol	Millimeters		
	Min.	Typ.	Max.
A			2.65
a1	0.10		0.30
b	0.35		0.49
b1	0.23		0.32
C		0.50	
c1	45° (typ.)		
D	17.7		18.1
E	10.00		10.65
e		1.27	
e3		16.51	
F	7.40		7.60
L	0.40		1.27
S	8° (max.)		

5.2 SO-28 packing information

Figure 32. SO-28 tube shipment (no suffix)

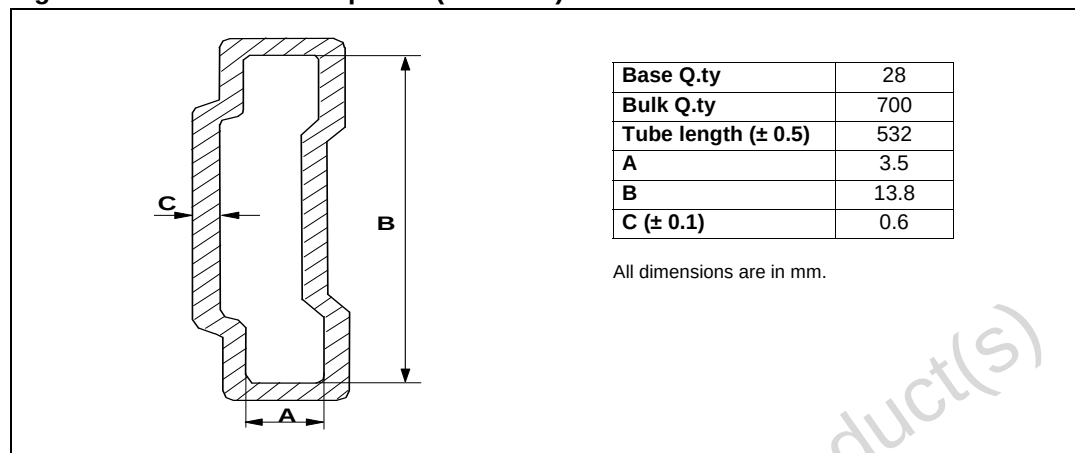
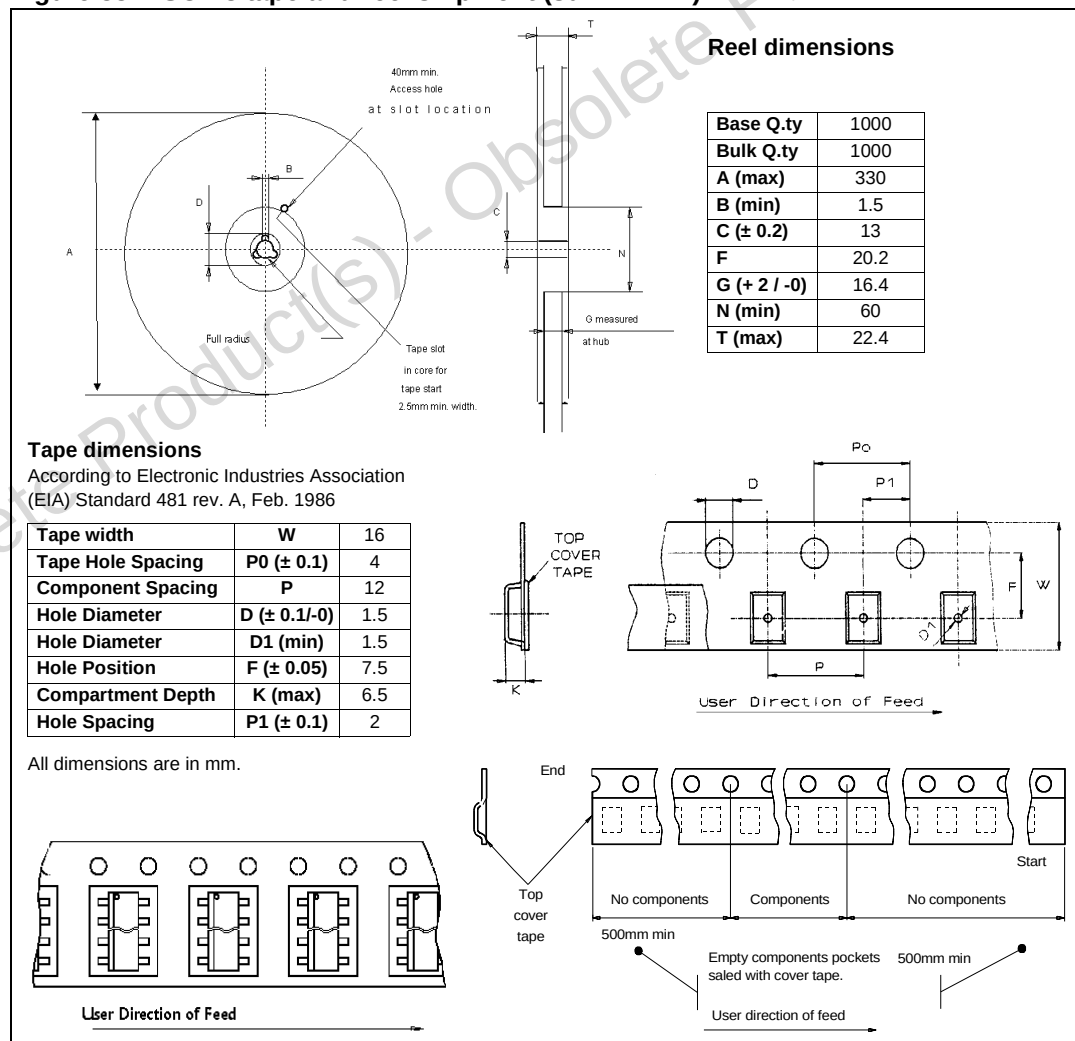


Figure 33. SO-28 tape and reel shipment (suffix "TR")



6 Revision history

Table 19. Document revision history

Date	Revision	Changes
21-Jun-2004	1	Initial release.
03-May-2006	2	E_{max} value (page 1). Current and voltage convention update (page 3). Configuration diagram (top view) & suggested connections for unused and n.c. pins insertion (page 3). 6 cm² Cu condition insertion in Thermal Data table (page 4). V_{CC} - output diode section update (page 5). Protections note insertion (page 5). On-state resistance Vs V_{CC} curve conditions correction (page 13). Turn-off voltage slope curve conditions correction (page 14). "Maximum turn-off current versus load inductance" curve modification (page 15). "SO-28 thermal impedance junction ambient single pulse": curve modification (page 17). Revision history table insertion (page 20). Disclaimers update (page 21).
25-Nov-2008	3	Document reformatted and restructured. Added contents, list of tables and figures. Added ECOPACK® packages information.
07-Feb-2011	4	Updated Figure 5: Switching characteristics
20-Sep-2013	5	Updated Disclaimer.

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